## Onsemi

### **Monolithic Dual Switching** Diode

## BAV74LT1G

#### Features

• These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS (EACH DIODE)**

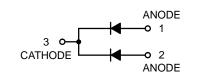
Rating	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	50	Vdc
Forward Current	١ <sub>F</sub>	200	mAdc
Peak Forward Surge Current	I <sub>FM(surge)</sub>	500	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1), $T_A = 25^{\circ}C$ Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\thetaJA}$	417	°C/W
Junction and Storage Temperature	TJ, Tstg	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = 1.0  $\times$  0.75  $\times$  0.062 in. 2. Alumina = 0.4  $\times$  0.3  $\times$  0.024 in 99.5% alumina.





**CASE 318** STYLE 9

#### **MARKING DIAGRAM**



JA = Device Code M = Date Code\*

= Pb–Free Package

(Note: Microdot may be in either location) \*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BAV74LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
BAV74LT3G	SOT–23 (Pb–Free)	10,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

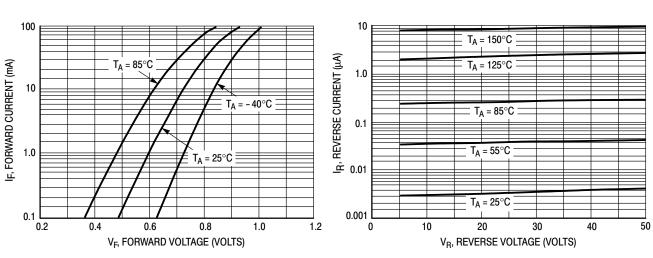
#### BAV74LT1G

#### ELECTRICAL CHARACTERISTICS ( $T_A = 25^{\circ}C$ unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Мах	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage $(I_{(BR)} = 5.0 \ \mu Adc)$	V <sub>(BR)</sub>	50	-	Vdc
Reverse Voltage Leakage Current, (Note 3) $(V_R = 50 \text{ Vdc}, T_J = 125^{\circ}\text{C})$ $(V_R = 50 \text{ Vdc})$	Ι <sub>R</sub>		100 0.1	μAdc
Diode Capacitance ( $V_R = 0, f = 1.0 \text{ MHz}$ )	CD	-	2.0	pF
Forward Voltage (I <sub>F</sub> = 100 mAdc)	V <sub>F</sub>	-	1.0	Vdc
Reverse Recovery Time (I <sub>F</sub> = I <sub>R</sub> = 10 mAdc, I <sub>R(REC)</sub> = 1.0 mAdc, measured at I <sub>R</sub> = 1.0 mA, R <sub>L</sub> = 100 $\Omega$ )	t <sub>rr</sub>	-	4.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. For each individual diode while the second diode is unbiased.



#### **CURVES APPLICABLE TO EACH ANODE**





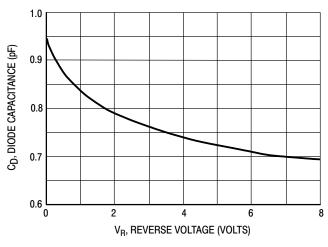


Figure 3. Capacitance

#### MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

D

3

TOP VIEW

SIDE VIEW

Нe

DETAIL A

-3X b

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SCALE 4:1

A\_\_\_\_ ' A1SOT-23 (TO-236) CASE 318 ISSUE AT

0.25

-L1

DETAIL A

END VIEW

DATE 01 MAR 2023

NDTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIM	MILLIMETERS			INCHES		
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.	
Α	0.89	1.00	1.11	0.035	0.039	0.044	
A1	0.01	0.06	0.10	0.000	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.017	0.020	
с	0.08	0.14	0.20	0.003	0.006	0.008	
D	2.80	2.90	3.04	0.110	0.114	0.120	
E	1.20	1.30	1.40	0.047	0.051	0.055	
e	1.78	1.90	2.04	0.070	0.075	0.080	
L	0.30	0.43	0.55	0.012	0.017	0.022	
L1	0.35	0.54	0.69	0.014	0.021	0.027	
Η <sub>E</sub>	2.10	2.40	2.64	0.083	0.094	0.104	
Т	0*		10*	0*		10*	



RECOMMENDED MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

### GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code

M = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

#### **STYLES ON PAGE 2**

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### MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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#### SOT-23 (TO-236) CASE 318 ISSUE AT

#### DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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